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List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Formation of Functional Conductive Carbon Coating on Si by C60 Ion Beam. Springer Proceedings in Physics, 2021, , 131-139.	0.2	5
2	Impact of Chemical Effects on Topography and Thickness of Modified GaN Surface Layers Bombarded by F and Ne Ions. Springer Proceedings in Physics, 2021, , 151-157.	0.2	0
3	In-situ transport and microstructural evolution in GaN Schottky diodes and epilayers exposed to swift heavy ion irradiation. Journal of Applied Physics, 2018, 123, 161539.	2.5	14
4	Single and molecular ion irradiation-induced effects in GaN: experiment and cumulative MD simulations. Journal Physics D: Applied Physics, 2017, 50, 505110.	2.8	4
5	Experimental study and MD simulation of damage formation in GaN under atomic and molecular ion irradiation. Vacuum, 2016, 129, 166-169.	3.5	8
6	Swift heavy ion irradiation of metal containing tetrahedral amorphous carbon films. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 162-166.	1.4	4
7	Effect of an increase in the density of collision cascades on the efficiency of the generation of primary displacements during the ion bombardment of Si. Semiconductors, 2016, 50, 989-995.	0.5	7
8	Modification of properties of metal containing carbon films by swift heavy ion irradiation. , 2014, , .		1
9	Effect of ion bombardment on the phase composition and mechanical properties of diamond-like carbon films. Journal of Surface Investigation, 2014, 8, 45-49.	0.5	12
10	Effect of growth conditions on carbon film properties. , 2014, , .		0
11	Nonlinear optical effect upon the irradiation of GaN with cluster ions. Semiconductors, 2014, 48, 446-450.	0.5	8
12	Defect clustering in irradiation of GaN by single and molecular ions. Vacuum, 2014, 105, 88-90.	3.5	11
13	Damage formation in Si under irradiation with PF _n + ions of different energies. Semiconductors, 2013, 47, 242-246.	0.5	12
14	Effect of collision cascade density on swelling and surface topography of GaN. Nuclear Instruments & Methods in Physics Research B, 2013, 315, 257-260.	1.4	3
15	Effects of defect clustering on optical properties of GaN by single and molecular ion irradiation. Journal of Applied Physics, 2013, 114, .	2.5	9
16	Atomistic simulation of damage production by atomic and molecular ion irradiation in GaN. Journal of Applied Physics, 2012, 112, .	2.5	18
17	Synthesis and tailoring of GaN nanocrystals at room temperature by RF magnetron sputtering. Radiation Effects and Defects in Solids, 2012, 167, 659-665.	1.2	4
18	Molecular effect on surface topography of GaN bombarded with PF ₄ ions. Vacuum, 2012, 86, 1638-1641.	3.5	9

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19	Model for radiation damage buildup in GaN. Nuclear Instruments & Methods in Physics Research B, 2012, 277, 80-83.	1.4	16
20	Electronic stopping dependence of ion beam induced modifications in GaN. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 890-893.	1.4	4
21	Residual stress in diamond-like carbon films: Role of growth conditions and ion irradiation. Journal of Surface Investigation, 2010, 4, 241-244.	0.5	9
22	Influence of ion irradiation on internal residual stress in DLC films. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 3107-3110.	1.4	13
23	Structural damage in ZnO bombarded by heavy ions. Vacuum, 2010, 84, 1058-1061.	3.5	22
24	Effect of pre-existing disorder on surface amorphization in GaN. Journal of Applied Physics, 2010, 108, 033505.	2.5	15
25	Effect of collision cascade density on radiation damage in SiC. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1247-1250.	1.4	10
26	Effects of the density of collision cascades: Separating contributions from dynamic annealing and energy spikes. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2701-2704.	1.4	8
27	Energy spike effects in ion-bombarded GaN. Journal Physics D: Applied Physics, 2009, 42, 085309.	2.8	29
28	Influence of ion bombardment on residual stresses in diamond-like carbon films. Journal of Surface Investigation, 2009, 3, 235-238.	0.5	2
29	Density of displacement cascades for cluster ions: An algorithm of calculation and the influence on damage formation in ZnO and GaN. Semiconductors, 2009, 43, 691-700.	0.5	18
30	Damage buildup and the molecular effect in Si bombarded with PF _n cluster ions. Nuclear Instruments & Methods in Physics Research B, 2007, 256, 207-210.	1.4	18
31	Using a chromatic-aberration correction system to achieve sub-1.6-nm resolutions of a focused-ion-beam microscope designed for characterization and processing. Russian Microelectronics, 2007, 36, 279-287.	0.5	5
32	Accumulation of structural defects in silicon irradiated with PF _n + cluster ions with medium energies. Semiconductors, 2007, 41, 5-10.	0.5	6
33	Effect of the density of collision cascades on ion implantation damage in ZnO. Journal of Applied Physics, 2007, 102, 083547.	2.5	37
34	Furthering the understanding of ion-irradiation-induced electrical isolation in wide band-gap semiconductors. Nuclear Instruments & Methods in Physics Research B, 2006, 243, 79-82.	1.4	4
35	Damage buildup in semiconductors bombarded by low-energy ions. Thin Solid Films, 2006, 515, 118-121.	1.8	0
36	Evaluation of focused O ⁺ ion beams as a tool for making resist masks by reactive etching. Russian Microelectronics, 2006, 35, 298-303.	0.5	2

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37	Mechanism for the molecular effect in Si bombarded with clusters of light atoms. Physical Review B, 2006, 73, .	3.2	28
38	A model of electrical isolation in GaN and ZnO bombarded with light ions. Semiconductors, 2004, 38, 1179-1186.	0.5	10
39	Delta-Doping of Monocrystalline Semiconductors by Al and Sb Implantation Using FIB Resistless Lithography. Russian Microelectronics, 2004, 33, 362-372.	0.5	0
40	Formation of surface amorphous layers in semiconductors under low-energy light-ion irradiation: Experiment and theory. Nuclear Instruments & Methods in Physics Research B, 2003, 212, 169-178.	1.4	16
41	Kinetics of growth of surface amorphous layers under irradiation of silicon with low-energy light ions. Semiconductors, 2003, 37, 340-346.	0.5	3
42	Model for electrical isolation of GaN by light-ion bombardment. Journal of Applied Physics, 2002, 92, 5740-5744.	2.5	21
43	Effect of ion species on implantation-produced disorder in GaN at liquid nitrogen temperature. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 782-786.	1.4	21
44	Molecular effect in semiconductors under heavy-ion bombardment: Quantitative approach based on the concept of nonlinear displacement spikes. Nuclear Instruments & Methods in Physics Research B, 2002, 194, 323-332.	1.4	12
45	Damage buildup in Si under bombardment with MeV heavy atomic and molecular ions. Journal of Applied Physics, 2001, 90, 3867-3872.	2.5	25
46	Effect of the density of collision cascades on implantation damage in GaN. Applied Physics Letters, 2001, 78, 2694-2696.	3.3	30
47	Ion beam induced amorphous→crystalline phase transition in Si: Quantitative approach. Nuclear Instruments & Methods in Physics Research B, 2000, 168, 375-388.	1.4	17
48	Damage accumulation in Si during N ⁺ and bombardment along random and channeling directions. Nuclear Instruments & Methods in Physics Research B, 1999, 149, 129-135.	1.4	15
49	Defect accumulation during room temperature N ⁺ irradiation of silicon. Nuclear Instruments & Methods in Physics Research B, 1996, 119, 491-500.	1.4	31
50	The role of point defects generated in the crystalline region in ion beam induced epitaxial crystallization of silicon. Radiation Effects and Defects in Solids, 1996, 139, 189-195.	1.2	5
51	The application of low angle Rutherford backscattering and channelling techniques to determine implantation induced disorder profile distributions in semiconductors. Nuclear Instruments & Methods, 1980, 168, 283-288.	1.2	26